

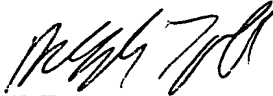
REMARKS

In this preliminary Amendment, Claims 3 - 7 and 10 - 11 are amended for to remove multiple dependent claims. A marked-up copy showing the changes made to the claims is attached. Applicants respectfully request that this amendment be entered before the calculation of the filing fee.

Kindly charge any additional fees due, or credit overpayment of fees, to Deposit Account No. 01-2135. (File No. 511.40998X00).

Respectfully submitted,

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Marked- up copy to show changes

IN THE CLAIMS:

3. (amended) The CMP abrasive according to Claim 1 ~~or 2~~, wherein said organic polymer is a compound containing either one or both of a nitrogen atom and an oxygen atom in a molecular structure.

4. (amended) The CMP abrasive according to ~~any one of Claims 1 to 3~~ Claim 1, wherein said organic polymer is a compound having an adsorption ratio of 50% or more with respect to silicon oxide particles of a specific surface area of 50 m²/g dispersed in water of pH 6 to 8.

5. (amended) The CMP abrasive according to ~~any one of Claims 1 to 4~~ Claim 1, wherein said organic polymer is a compound having an adsorption ratio of 40% or more with respect to silicon nitride particles of a specific surface area of 3.3 m²/g dispersed in water of pH 6 to 8.

6. (amended) The CMP abrasive according to ~~any one of Claims 1 to 5~~ Claim 1, wherein the sedimentation speed of cerium oxide particles is 20 μm/s or less.

7. (amended) The CMP abrasive according to ~~any one of Claims 1 to 6~~ Claim 1, wherein said organic polymer is polyvinyl pyrrolidone.

10. (amended) A method for polishing a substrate comprising polishing by moving a substrate on which a film to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive according to ~~any one of claims 1 to 9~~ Claim 1 between the film to be polished and the

polishing cloth.

11. (amended) A method for manufacturing a semiconductor device comprising a step of polishing a film to be polished by moving a substrate on which the film to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive according to ~~any one of Claims 1 to 9~~ Claim 1 between the film to be polished and the polishing cloth.